

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

Sheet 1 of 8

Application Number	10/775,999
Filing Date	February 10, 2004
First Named Inventor	Faris
Group Art Unit	1792
Examiner Name	Binh X. Tran
Attorney Docket Number	Reveo-0179

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		4,370,176	25-Jan-83	Bruel	148	1.5	
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		4,471,003	11-Sep-84	Cann	427	34	
		4,479,846	30-Oct-84	Smith et al.	156	603	
		4,500,563	19-Feb-85	Ellenberger et al.	427	38	
		4,585,945	29-Apr-86	Bruel et al.	250	492.2	
		4,816,420	28-Mar-89	Bozler et al.	437	2	
		4,837,182	06-Jun-89	Bozler et al.	437	82	
		4,846,931	11-Jul-89	Gmitter et al.	156	633	
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		5,882,987	16-Mar-99	Srikrishnan	438	458	
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		6,059,877	09-May-00	Bruel	117	35	
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		6,137,110	24-Oct-00	Pellin et al.	250	423	
/BT/		6,146,979	14-Nov-00	Henley et al.	438	458	

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		6,387,736	May 2002	Cao et al.	438	149	
		6,309,945	Oct 2001	Sato	437	409	
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Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>	Application Number	10775,999
	Filing Date	February 10, 2004
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	Group Art Unit	1792
	Examiner Name	Binh X. Tran
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	WO 98/20543A2	14-May-98	PCT				
	WO 98/33209	30-Jul-98	PCT				
	WO 99/05711A1	4-Feb-99	PCT				
	WO 99/08316A1	18-Feb-99	PCT				
	WO 99/35674A1	15-Jul-99	PCT				
	WO 99/39377A1	5-Aug-99	PCT				
	WO 99/66559A1	23-Dec-99	PCT				
	WO 00/03429A1	20-Jan-00	PCT				X
	WO 00/24059A1	27-Apr-00	PCT				X
	WO 00/24054A1	27-Apr-00	PCT				X
	WO 00/46847A1	10-Aug-00	PCT				
	WO 00/48238A1	17-Aug-00	PCT				
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Examiner Signature	/Binh Tran/	Date Considered	11/14/2008
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Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>	Application Number	10/775,999
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	Examiner Name	Binh X. Tran
Sheet 5 of 8	Attorney Docket Number	Reveo-0179

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Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>	Application Number	10/775,999
	Filing Date	February 10, 2004
	First Named Inventor	Faris
	Group Art Unit	1792
	Examiner Name	Binh X. Tran
Sheet 8 of 8	Attorney Docket Number	Reveo-0179

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Examiner Signature	/Binh Tran/	Date Considered	11/14/2008
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